

Q.1. a) For the field to represent an electrostatic field we must have $\nabla \times \vec{E} = 0$. Now

$$\begin{aligned}\nabla \times \vec{E} &= \begin{vmatrix} \hat{x} & \hat{y} & \hat{z} \\ \frac{\partial}{\partial x} & \frac{\partial}{\partial y} & \frac{\partial}{\partial z} \\ (xz^2 - y^2) & -2xy & 0 \end{vmatrix} \\ &= \hat{x} (0 - 0) + \hat{y} (0 - 0) + \hat{z} (-2y + 2y) \\ &= 0\end{aligned}$$

Hence the given vector field can represent an electrostatic field.

$$\begin{aligned}b) \quad \vec{E} &= \frac{Q}{4\pi\epsilon_0} \frac{[(x-x_0)\hat{x} + (y-y_0)\hat{y} + (z-z_0)\hat{z}]}{[(x-x_0)^2 + (y-y_0)^2 + (z-z_0)^2]^{3/2}} \\ &= \frac{Q}{4\pi\epsilon_0} \frac{[(0-0)\hat{x} + (2-0)\hat{y} + (0-2)\hat{z}]}{[0^2 + 2^2 + 2^2]^{3/2}} \\ &= \frac{Q}{4\pi\epsilon_0} \frac{[2\hat{y} - 2\hat{z}]}{8^{3/2}} = \frac{10^{-6} \times 9 \times 10^9 \times 2(\hat{y} - \hat{z})}{8^{3/2}} \\ &= 795.5 (\hat{y} - \hat{z})\end{aligned}$$

c) According to Gauss's law

$$\nabla \cdot \vec{E} = \rho/\epsilon_0$$

For the given \vec{E} , we have

$$\begin{aligned}\nabla \cdot \vec{E} &= \frac{A}{R} \left[\frac{1}{r^2} \frac{\partial}{\partial r} (-r^2 \cos \theta) + \frac{1}{r \sin \theta} \frac{\partial}{\partial \theta} (\sin^2 \theta) \right] \\ &= \frac{A}{R} \left[-\frac{2}{r} \cos \theta + \frac{2}{r} \cos \theta \right] = 0\end{aligned}$$

Hence $\rho = 0$

d) Inside the conducting plate $\vec{E} = 0$. Thus the surface charges must produce an electric field $\vec{E}_s = -E_0 \hat{z}$. If charge density is σ_f , then

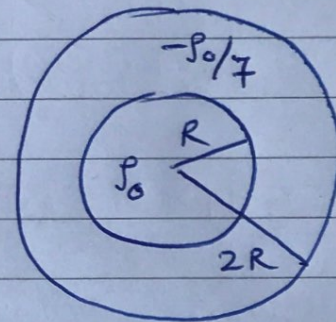
$$E_0 = \frac{\sigma_f}{\epsilon_0}$$

$$\text{or } \sigma_f = \epsilon_0 E_0$$

2)

a) Gauss's law

$$\oint \vec{E} \cdot d\vec{a} = \frac{Q_{\text{enc}}}{\epsilon_0}$$



For $r < R$

- \vec{E} is radial and independent of θ and ϕ .

- Hence for $r < R$ $\oint \vec{E} \cdot d\vec{a} = 4\pi r^2 E$

$$- Q_{\text{enc}} = \frac{4\pi}{3} r^3 \rho_0$$

Hence

$$4\pi r^2 E = \frac{4\pi}{3} \rho_0 r^3$$

$$\text{or } E = \frac{\rho_0 r}{3\epsilon_0}$$

$$\text{Hence } \vec{E} = \frac{\rho_0 r}{3\epsilon_0} \hat{r} = \frac{\rho_0 \vec{r}}{3\epsilon_0}$$

- For $R < r < 2R$

$$\oint \vec{E} \cdot d\vec{a} = 4\pi r^2 E$$

$$\oint Q_{\text{enc}} = \int_0^R \frac{4\pi}{3} R^3 \rho_0 + \frac{4\pi}{3} (r^3 - R^3) \left(-\frac{\rho_0}{7}\right)$$

$$= \frac{4\pi}{3} \rho_0 \left(\frac{8R^3}{7} - \frac{r^3}{7} \right)$$

Here $4\pi r^2 E = \frac{4\pi \rho_0}{3\epsilon_0} \left(\frac{8R^3}{7} - \frac{r^3}{7} \right)$

$$\vec{E} = \frac{\rho_0}{3\epsilon_0 r^2} \left(\frac{8R^3}{7} - \frac{r^3}{7} \right) \hat{r}$$

For $r > 2R$

$$Q_{enc} = \frac{4\pi R^3}{3} \rho_0 + \frac{4\pi}{3} (8R^3 - R^3) \cdot \left(-\frac{\rho_0}{7} \right)$$

$$= 0$$

Thus $\vec{E} = 0$ for $r > 2R$

b) $\nabla \cdot \vec{E} \Big|_{r=3R/2} = \frac{\rho(3R/2)}{\epsilon_0} = -\frac{\rho_0}{7\epsilon_0}$

$$\nabla \times \vec{E} \Big|_{r=3R/2} = 0$$

3) a) Charge on the conducting sphere resides on the surface.

Such a charge distribution produces zero field inside and outside for $r > R$

$$\vec{E} = \frac{Q}{4\pi\epsilon_0 r^2} \hat{r}$$

Potential at the surface

$$V(r=R) = \frac{Q}{4\pi\epsilon_0 R}$$

Since $\vec{E} = 0$ for $r < R$ we have

$$V(r < R) = \frac{Q}{4\pi\epsilon_0 R}$$

$$V(r > R) = \frac{Q}{4\pi\epsilon_0 r}$$

- 6) V depends only on radial coordinate r .
Hence work done in moving a unit positive charge will be

$$\begin{aligned} W = \Delta V &= V(r=3R) - V(r=2R) \\ &= \frac{Q}{4\pi\epsilon_0(3R)} - \frac{Q}{4\pi\epsilon_0(2R)} \\ &= -\frac{Q}{4\pi\epsilon_0 \times 6R} \end{aligned}$$

4)

- a) Gauss's law in the presence of dielectric

$$\oint \vec{D} \cdot d\vec{a} = Q_{\text{free}}$$

\vec{D} will be along \hat{z}

Taking surface S_1 we have

$$D \cdot A = \sigma_f \cdot A \Rightarrow D = \sigma_f; \quad \vec{D} = \sigma_f \hat{z}$$

Similarly

$$\vec{D} = \sigma_f \hat{z} \text{ inside dielectric}$$

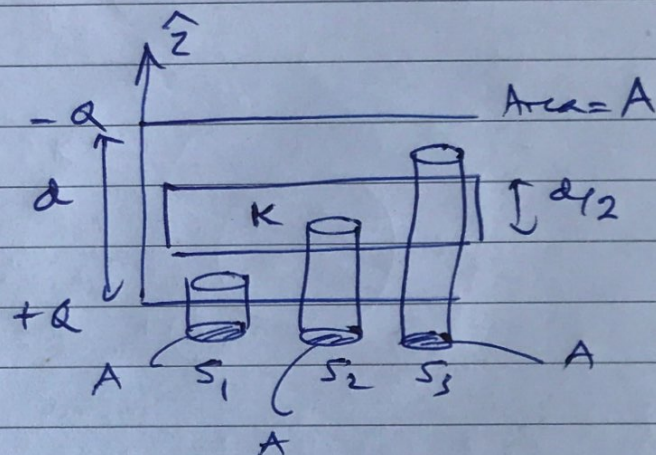
$$\text{Since } \vec{E} = \vec{D}/\epsilon \text{ inside dielectric}$$

$$= \vec{D}/\epsilon_0 \text{ in free space}$$

we get

$$\vec{E} = \frac{\sigma_f}{\epsilon_0} \hat{z} \text{ in air}$$

$$= \frac{\sigma_f}{\epsilon_0 K} \hat{z} \text{ in dielectric}$$



(3)

$$\begin{aligned}
 b) \quad \vec{P} &= \epsilon_0 \chi \vec{E} = \epsilon_0 (K-1) \vec{E} \\
 &= \frac{\epsilon_0 (K-1) \sigma_f}{\epsilon_0 K} \hat{z} = \frac{(K-1) \sigma_f}{K} \hat{z}
 \end{aligned}$$

$$\rho_b = -\vec{\nabla} \cdot \vec{P} = 0$$

$$\sigma_b = \vec{P} \cdot \hat{n}$$

Upper surface of dielectric $\hat{n} = \hat{z}$ and
 lower surface of dielectric $\hat{n} = -\hat{z}$.

Thus

$$\begin{aligned}
 \sigma_b &= \frac{(K-1) \sigma_f}{K} \text{ at upper surface} \\
 &= -\frac{(K-1) \sigma_f}{K} \text{ at lower surface}
 \end{aligned}$$